

# DOCUMENT CHANGE REQUEST

496 DCR number Changes required for: General Originator: S Jeffery - ESCC Date: 2009/04/14 Organisation: ESA/ESTEC Date sent: 2009/04/14 Status: IMPLEMENTED Title: Transistors High Voltage NPN, based on type 2N5551 Number: 5201/019 Issue: Other documents affected: Page: See attachment Paragraph: See attachment Original wording: Proposed wording: Various editorial and technical changes as detailed in the attachment, which are required to make this detail spec clear, complete and consistent with the standard format and content of specifications for similar Part Types. Note that this DCR replaces the withdrawn DCR 465. Justification: Improve the appearance, content and clarity of the spec. Attachments: 5201019\_Issue\_5\_-\_Draft\_B.pdf, null Modifications: N/A Approval signature: surtes Date signed: 2009-04-14

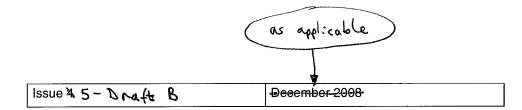


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# TRANSISTORS, HIGH VOLTAGE, NPN

## **BASED ON TYPE 2N5551**

ESCC Detail Specification No. 5201/019







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# **DOCUMENTATION CHANGE NOTICE**

(Refer to https://escies.org for ESCC DCR content)

DCR No.	CHANGE DESCRIPTION
433,482 4342	Specification up issued to incorporate editorial and technical changes per DCRs.
(tbd	



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#### 1. **GENERAL**

#### 1.1 SCOPE

This specification details the ratings, physical and electrical characteristics and test and inspection data for the component type variants and/or the range of components specified below. It supplements the requirements of, and shall be read in conjunction with, the ESCC Generic Specification listed under Applicable Documents.

#### 1.2 APPLICABLE DOCUMENTS

The following documents form part of this specification and shall be read in conjunction with it:

- (a) ESCC Generic Specification No. 5000
- (b) MIL-STD-750, Test Methods and Procedures for Semiconductor Devices

#### 1.3 TERMS, DEFINITIONS, ABBREVIATIONS, SYMBOLS AND UNITS

For the purpose of this specification, the terms, definitions, abbreviations, symbols and units specified in ESCC Basic Specification No. 21300 shall apply.

#### 1.4 THE ESCC COMPONENT NUMBER AND COMPONENT TYPE VARIANTS

#### 1.4.1 The ESCC Component Number

The ESCC Component Number shall be constituted as follows:

Example: 520101901

• Detail Specification Reference: 5201019

Component Type Variant Number: 01 (as required)

## 1.4.2 <u>Component Type Variants</u>

The component type variants applicable to this specification are as follows:

Variant Number	Based on Type	Case	Lead/Terminal Material and/or Finish	Weight max g
01	2N5551	TO-18	D2	0.4
02	2N5551	TO-18	D3 or D4	0.4
04	2N5551	CCP (3 Terminal)	2	0.06
05	2N5551	CCP (3 Term(nal)	4	0.06
06	2N5551	TO-39	D2	1.5
07	2N5551	TO-39	D3 or D4	1.5
08	2N5551	CCP (4 Terminal)	2	0.06
09	2N5551	CCP (4 Terminal)	) 4	0.06

The lead/terminal material and/or finish shall be in accordance with the requirements of ESCC Basic

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Specification No. 23500.

#### 1.5 <u>MAXIMUM RATINGS</u>

The maximum ratings shall not be exceeded at any time during use or storage.

Maximum ratings shall only be exceeded during testing to the extent specified in this specification and when stipulated in Test Methods and Procedures of the ESCC Generic Specification.

Characteristics	Symbols	Maximum Ratings	Unit	Remarks
Collector-Base Voltage	V <sub>CBO</sub>	180	V	Over entire
Collector-Emitter Voltage	V <sub>CEO</sub>	160	V	operating temperature
Emitter-Base Voltage	V <sub>EBO</sub>	6	٧	range
Collector Current For TO-18 and TO-39 For CCP	I <sub>C</sub>	600 500	mA	Continuous
Power Dissipation For TO-18, TO-39 and CCP	P <sub>tot1</sub>	0.36	w W	At T <sub>amb</sub> ≤ +25°C
For TO-18 and TO-39	P <sub>tot</sub> 2	1.2	$\frac{\sqrt{\sqrt{\sqrt{2}}}}{\sqrt{\sqrt{2}}}$	At T <sub>case</sub> ≤ +25°0
Operating Temperature Range	T <sub>op</sub>	-65 to +200	°C	Note § 2
Storage Temperature Range	T <sub>stg</sub>	-65 to +200	°C	Note § 2
Soldering Temperature For TO-18 and TO-39 For CCP	T <sub>sol</sub>	+260 +245	°C	Note & 3 Note § 4

attached

NOTES:

1. For T<sub>amb</sub> or T<sub>case</sub> > +25°C, derate linearly to 0W-at +200°C.

2. When-mounted-on-an-8-x-10-x-0.6mm-seramic-substrate-

2. So For Variants with tin-lead plating or hot solder dip lead finish all testing performed at T<sub>amb</sub> > +125°C shall be carried out in a 100% inert atmosphere.

3. 4. Duration 10 seconds maximum at a distance of not less than 1.5mm from the device body and the same lead shall not be resoldered until 3 minutes have elapsed.

Duration 5 seconds maximum and the same terminal shall not be resoldered until 3 minutes have elapsed.

1. Thermal Resistance, Junction-to-Case applies to all TO-18 and TO-39 packaged Variants.

Thermal Resistance,				
Junction-to-Ambient	$R_{th(j-a)}$	486	°C/W	
Thermal Resistance,				
Junction-to-Case	R <sub>th(j-c)</sub>	145.8	°C/W	Note 1



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Characteristics	Symbols		Units		
		Drift	Abso		
		Value Δ	Min	Max	
Collector-Base Cut-off Current	I <sub>CBO</sub>	±5 or (1) ±100%	-	50	nA
Collector-Emitter Saturation Voltage 2	V <sub>CE(sat)2</sub>	±30 or (1) ±15%	-	200	mV
Forward-Current Transfer Ratio 2	h <sub>FE2</sub>	±15%	80	250	-

#### **NOTES:**

1. Whichever is the greater referred to the initial value.

#### 2.6 INTERMEDIATE AND END-POINT ELECTRICAL MEASUREMENTS

Unless otherwise specified, the measurements shall be performed at  $T_{amb}$ =+22  $\pm 3^{\circ}$ C.

The test methods and test conditions shall be as per the corresponding test defined in Room Temperature Electrical Measurements.

The limit values for each characteristic shall not be exceeded.

Characteristics	Symbols	Lin	Units	
		Min	Max	
Collector-Base Cut-off Current	I <sub>CBO</sub>	-	50	nA
Collector-Emitter Saturation Voltage 2	V <sub>CE(sat)2</sub>	-	200	mV
Forward-Current Transfer Ratio 2	h <sub>FE2</sub>	80	250	_

#### 2.7 **POWER BURN-IN CONDITIONS**

Characteristics	Symbols	Test Conditions	Units
Ambient Temperature	T <sub>amb</sub>	+25 to +50	°C
Power Dissipation	P <sub>tot</sub>	As per Maximum Ratings. Ptot1 derated at the chosen Tamb Maing the	W
Collector-Base Voltage	V <sub>CB</sub>	90	V

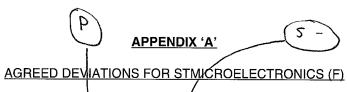
**OPERATING LIFE CONDITIONS** 2.8

The conditions shall be as specified for Power Burn-in.



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	}		/				
ITEMS AFFECTED		DESC	RIPTION OF	DEVIATIONS	3	74.	
Deviations from Production Control- Chart F2	Special In-process Control Internal Visual Inspection. For CCP packages the criteria specified for voids in the fillet and minimum die mounting material around the visible die perimeter for die mounting defects may be omitted providing that a radiographic inspection to verify the die-attach process is performed on a sample basis in accordance with STMicroelectronics procedure 0076637.						
Deviations from Room Temperature Electrical Measurements	All AC character may be consided has been performeasurements.  A summary of Purchase Order	ered guaran ormed on the s per the Det the pilot lot t er.	teed but not to wafer lot which ail Specification esting shall be	ested if succe ch includes A on. provided if re	ssful pil C chara	ot lot te acteristic	sting
	Characteristics Symbols		MIL-STD-750 Test Method	Test Conditions	Limits		Units
					Min.	Max.	
	High Frequency Small-Signal Short-Circuit Forward-Current Transfer Ratio	h <sub>fe2</sub>	3306	V <sub>CE</sub> =10V I <sub>C</sub> =10mA f=20MHz Note 2	2.5	-	-
	Emitter-Base Capacitance	C <sub>ebo</sub>	3240	V <sub>EB</sub> =500mV I <sub>C</sub> =0A f=1MHz Note 2	-	45	pF
Deviations from High and Low Temperatures Electrical Measurements	All characteristics specified may be considered guaranteed but not tested if successful pilot lot testing has been performed on the wafer lot which includes characteristic measurements at high and low temperatures per the Detail Specification. A summary of the pilot lot testing shall be provided if required by the Purchase Order.						
Deviations from Screening Tests - Chart F3	Solderability is Order.	not applicat	ole unless spec	cifically stipula	ated in t	he Purc	 chase